

October 2007

# 2N7002DW

# N-Channel Enhancement Mode Field Effect Transistor

## **Features**

- Dual N-Channel MOSFET
- · Low On-Resistance
- · Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- · Lead Free/RoHS Compliant

### SC70-6 (SOT363)





Marking: 2N

## Absolute Maximum Ratings \* T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
V <sub>DSS</sub>	Drain-Source Voltage		60	V
V <sub>DGR</sub>	Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		60	V
$V_{GSS}$	Gate-Source Voltage	Continuous Pulsed	±20 ±40	V
I <sub>D</sub>	Drain Current	Continuous Continuous @ 100°C Pulsed	115 73 800	mA
$T_{J}$ , $T_{STG}$	Junction and Storage Temperature Range		-55 to +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

## **Thermal Characteristics**

Symbol	Parameter	Value	Units	
P <sub>D</sub>	Total Device Dissipation Derating above TA = 25°C	200 1.6	mW mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	625	°C/W	

<sup>\*</sup> Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, Minimun land pad size,

# **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	TYP	MAX	Units
Off Charac	teristics (Note1)					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> =10uA	60	78	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V, @T <sub>C</sub> = 125°C	-	0.001 7	1.0 500	uA
I <sub>GSS</sub>	Gate-Body Leakage	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	0.2	±10	nA
On Charac	teristics (Note1)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	1.0	1.76	2.0	V
R <sub>DS(ON)</sub>	Satic Drain-Source On-Resistance	$V_{GS} = 5V, I_D = 0.05A,$ $V_{GS} = 10V, I_D = 0.5A, @T_j = 125°C$	-	1.6 2.53	7.5 13.5	Ω
I <sub>D(ON)</sub>	On-State Drain Current	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V	0.5	1.43	-	А
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A	80	356.5	-	mS
Dynamic (	Characteristics					
C <sub>iss</sub>	Input Capacitance		-	37.8	50	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	12.4	25	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	6.5	7.0	pF
Switching	Characteristics					
t <sub>D(ON)</sub>	Turn-On Delay Time	$V_{DD} = 30V, I_{D} = 0.2A, V_{GEN} = 10V$	-	5.85	20	no
t <sub>D(OFF)</sub>	Turn-Off Delay Time	$R_L = 150\Omega$ , $R_{GEN} = 25\Omega$	-	12.5	20	ns

Note1 : Short duration test pulse used to minimize self-heating effect.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

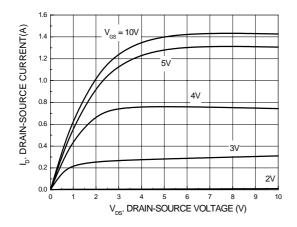


Figure 3. On-Resistance Variation with Temperature

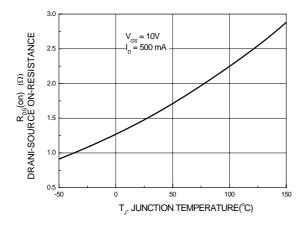


Figure 5. Transfer Characteristics

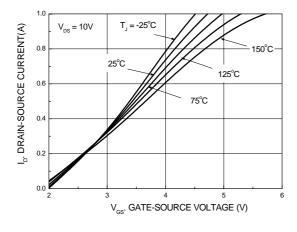


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

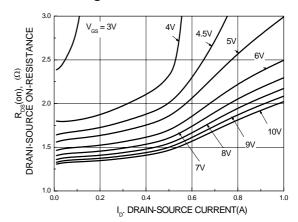


Figure 4. On-Resistance Variation with Gate-Source Voltage

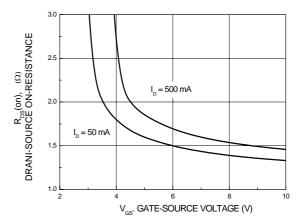
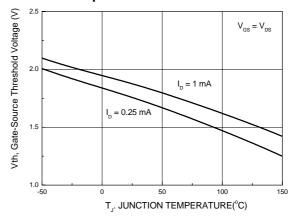


Figure 6. Gate Threshold Variation with Temperature



# **Typical Performance Characteristics**

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

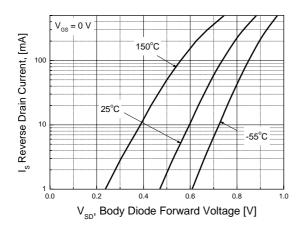
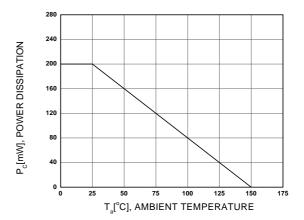
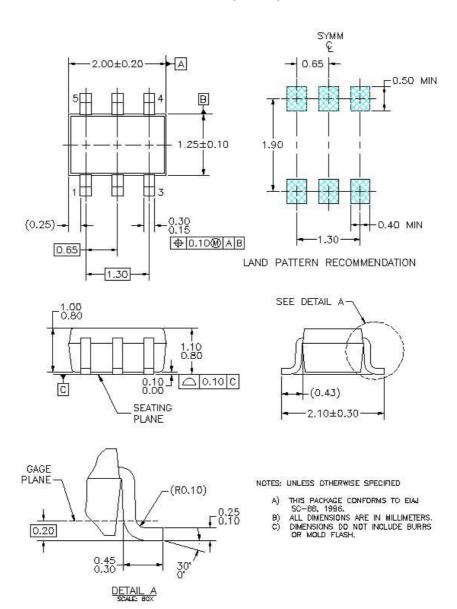


Figure 8. Power Derating



# **Package Dimensions**

## SC70-6 (SOT-363)







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